| Process | | NR71 1500P |
|---|---|---|
| Dehydration Bake (hot plate) | temp (˚C) | 200 |
| | time (min) | 5 |
| Spin coating NR71-1500P | Speed/acc (rpm) | 300 |
| | time (s) | 3 |
| | speed (rpm) | 3000 |
| | acceleration (rpm/s) | 5000 |
| | time (s) | 45 |
| Soft-bake (hotplate) | temp (˚C) | 150 |
| | time (s) | 60 |
| Expose (12mW/cm$^2$) | mode | HC |
| | time (s) | 27 |
| Post Exposure Bake (hot plate) | temp (˚C) | 100 |
| | time (s) | 60 |
| Develop | developer | RD 6 |
| | developer: di water ratio | No mix |
| | time (sec) (approx.) | 18 |
| Rinse in DI water | time (min) | 2 |

NB:

1. SC: Soft Contact; HC: Hard Contact; VC: Vacuum Contact; LVC: Low Vacuum Contact
2. Development of NR71-1500P is accomplished in a basic water solution (RD6)
3. If exposure is insufficient, bleaching within the exposed areas will be observed after development. This should not happen with sufficiently exposed resist surface which should be fully cross-linked.
4. NR71-1500P DOES NOT dissolve well in acetone. Use 1165 remover, RR5 or RR4 strippers.
5. These are results using a bare Silicon substrate. Films on substrates and/or use of other types of substrates may affect the exposure and/or development time. Adjust as needed.
6. Use of this process data should act as a guide to developing and/or refining your process rather than being adopted as is. The process was used to resolve a minimum feature size of 2 µm.